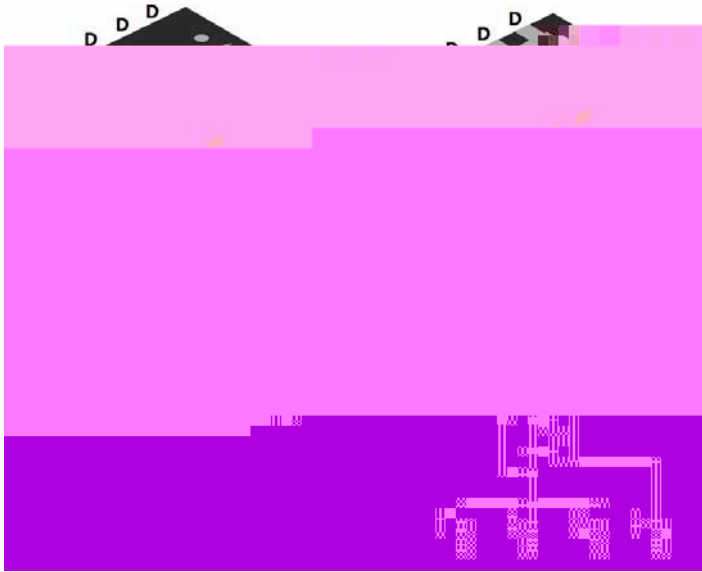




## P-Channel Enhancement Mode Field Effect Transistor



## Product Summary

$V_{DS}$	-100V
$I_D$	-15A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	110m
$R_{DS(ON)}$ ( at $V_{GS}=4.5V$ )	120m
100% EAS Tested	

## General Description

Split gate trench MOSFET technology  
Excellent package for heat dissipation  
High density cell design for low  $R_{DS(ON)}$   
Part no. with suffix "Q" means AEC-Q101 qualified

## Applications

Power switching application  
Uninterruptible power supply  
DC-DC converter  
12V, 24V and 48V Automotive systems

Absolute Maximum Ratings ( $T_A=25$  unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-source Voltage		$V_{DS}$	-100	V
Gate-source Voltage		$V_{GS}$	$\pm 20$	V
Drain Current	$T_A=25$	$I_D$	-3.9	A
	$T_A=100$		-2.5	
	$T_C=25$		-15	
	$T_C=100$		-9.5	
Pulsed Drain Current <sup>A</sup>		$I_{DM}$	-35	A
Avalanche energy <sup>B</sup>		EAS	64	mJ
Total Power Dissipation <sup>C</sup>	$T_A=25$	$P_D$	2.5	W
	$T_A=100$		1	
	$T_C=25$		43	
	$T_C=100$		17.2	
Junction and Storage Temperature Range		$T_J, T_{STG}$	-55 +150	

## Thermal resistance

Parameter		Symbol	Typ	Max	Units
Thermal Resistance Junction-to-Ambient <sup>D</sup>	Steady-State	$R_{JA}$	40	50	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{JC}$	2.4	2.9	

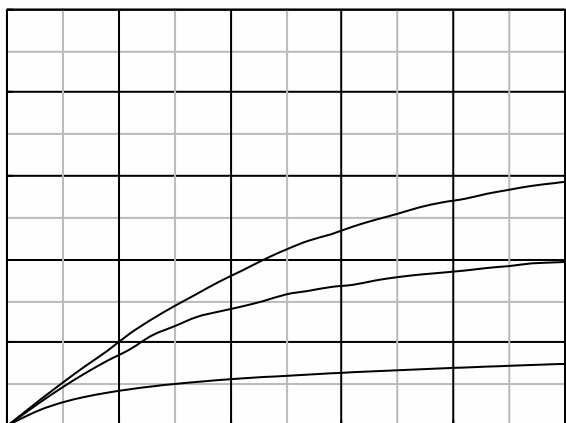
## Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJQ15GP10AQ	F1	Q15GP10A	5000	10000	100000	13" reel





Typical Electrical and Thermal Characteristics Diagrams





# YJQ15GP10AQ

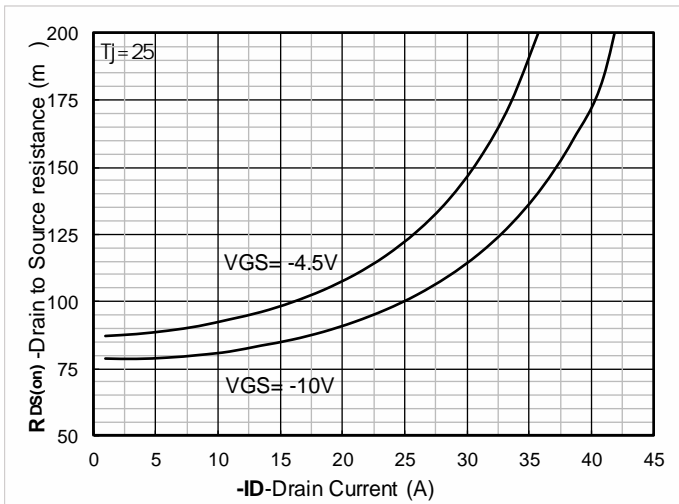


Figure 7. RDS(on) VS Drain Current

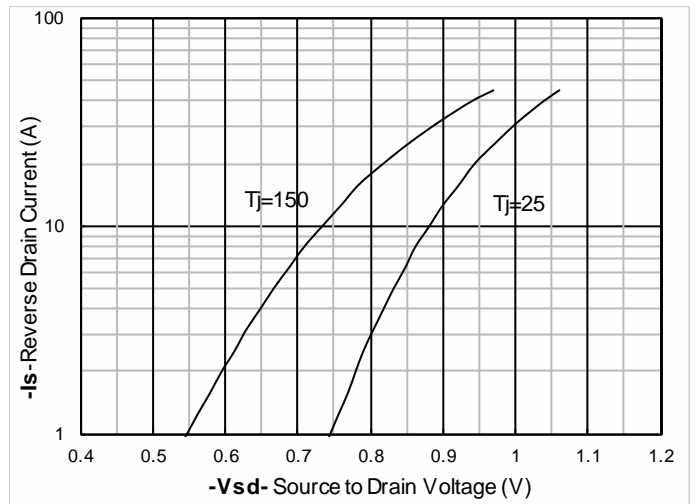


Figure 8. Forward characteristics of reverse diode

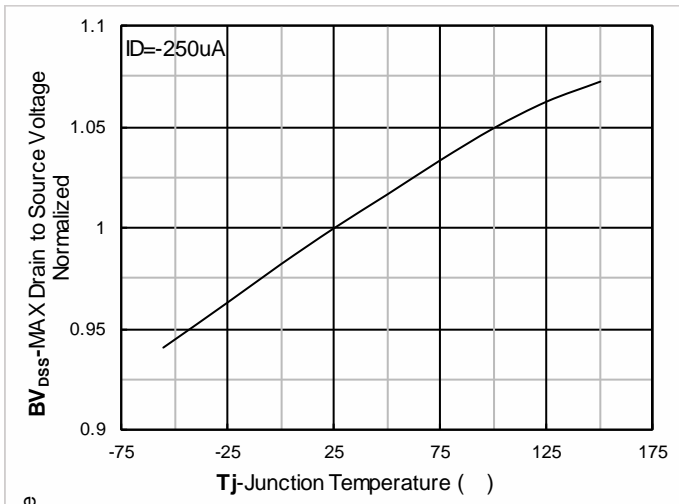


Figure 9. Normalized breakdown voltage

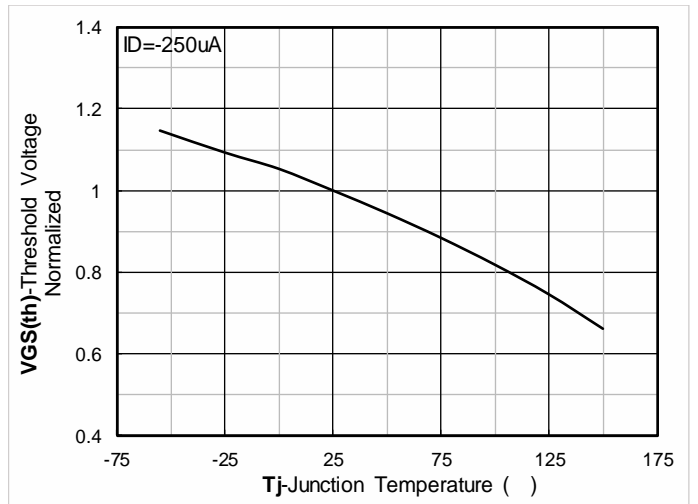
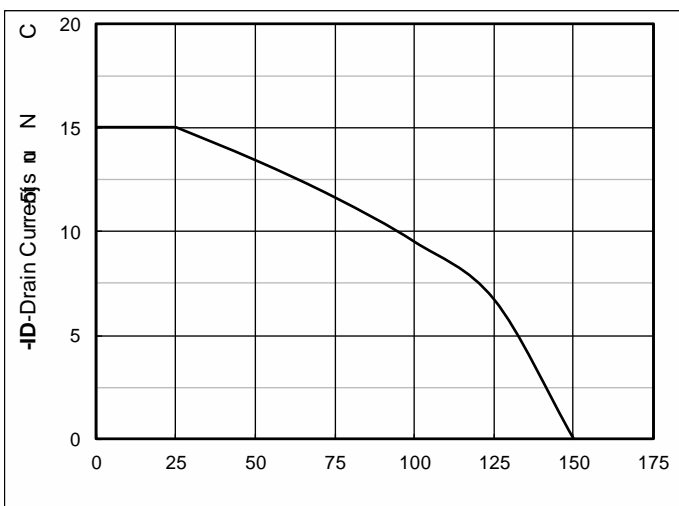


Figure 10. Normalized Threshold voltage







# YJQ15GP10AQ

## DFN3333-8L Package information

